Description

The AR0552S2 is a low capacitance TVS array, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR0552S2 has an ultra-low capacitance with a typical value at 0.4pF, and complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±20kV contact discharge. It is assembled into a 6-Pin lead-free SOT23-6 package. The low capacitance array make it ideal for four high speed data and transmission line. This device is optimized for ESD protection of portable electronics.

Features

- Ultra low leakage: nA level
- Operating voltage: 5V
- Low clamping voltage
- Two data lines and one power line protects
- Complies with following standards:
  - IEC 61000-4-2 (ESD) immunity test
    - Air discharge: ±25kV
    - Contact discharge: ±20kV
  - IEC61000-4-5 (Lightning) 5A (8/20μs)
- RoHS Compliant

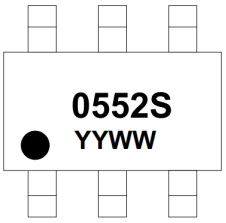
Mechanical Characteristics

- Package: SOT23-6
- Lead Finish: Matte Tin
- Case Material: “Green” Molding Compound.
- Terminal Connections: See Diagram Below
- Marking Information: See Below

Applications

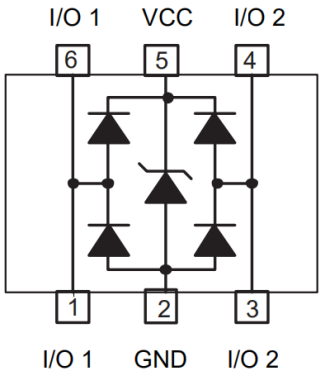
- USB 2.0 Power and Data lines protection
- Digital Visual Interface (DVI)
- Monitors and Flat Panel Displays
- Gigabit Ethernet
- Ethernet port: 10/100Mb/s
- SIM card protection

Marking Information



0552S = Device Marking Code
YYWW = Date Code
Dot denotes Pin1

Dimensions and Pin Configuration



Circuit and Pin Schematic

Ordering Information

Part Number	Packaging	Reel Size
AR0552S2	3000/Tape & Reel	7 inch

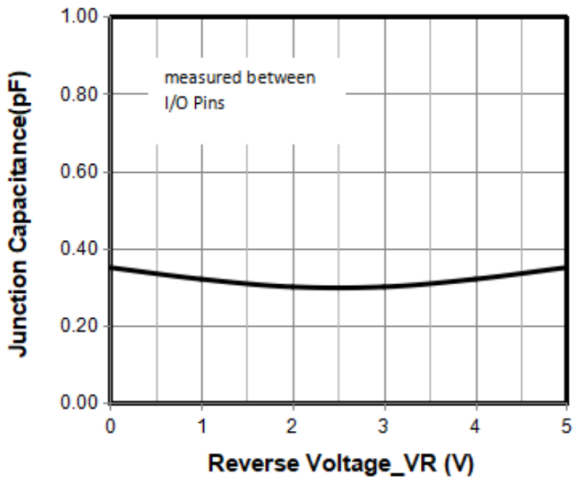
Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	75	W
Peak Pulse Current (8/20μs)	I_{PP}	5	A
ESD per IEC 61000−4−2 (Air) ESD per IEC 61000−4−2 (Contact)	V_{ESD}	±25 ±20	kV
Operating Temperature Range	T_J	−55 to +125	°C
Storage Temperature Range	Tstg	−55 to +150	°C

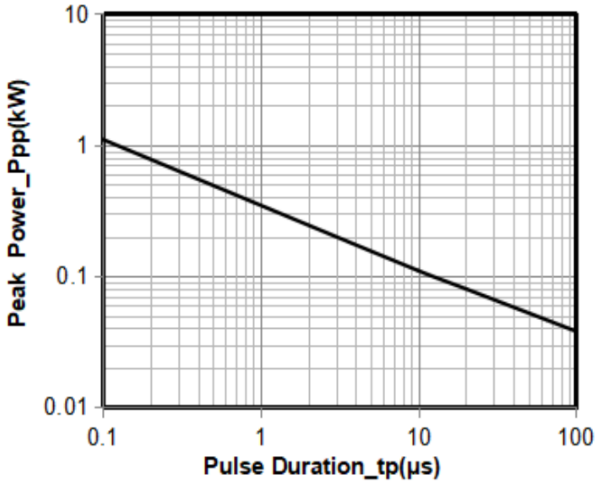
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	V_{RWM}			5	V	Any I/O pin to ground
Breakdown Voltage	V_{BR}	6			V	I_T = 1mA, any I/O pin to ground
Reverse Leakage Current	I_R			0.2	μA	V_{RWM} = 5V, any I/O pin to ground
Clamping Voltage	V_C			10	V	I_{PP} = 1A (8 x 20μs pulse), any I/O pin to ground
Clamping Voltage	V_C			15	V	I_{PP} = 5A (8 x 20μs pulse), any I/O pin to ground
Junction Capacitance	C_J		0.3	0.4	pF	VR = 0V, f = 1MHz, between I/O pins
Junction Capacitance	C_J		0.6	0.8	pF	VR = 0V, f = 1MHz, any I/O pin to ground

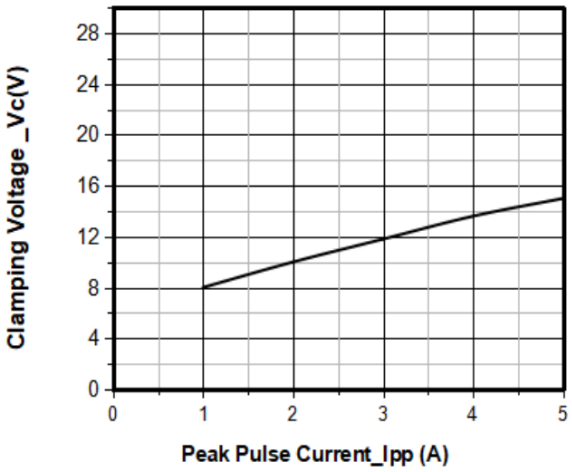
Typical Performance Characteristics (T_A=25°C unless otherwise Specified)



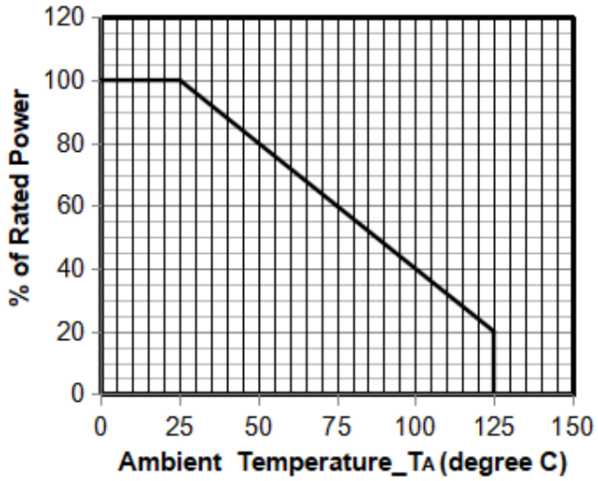
Junction Capacitance vs. Reverse Voltage



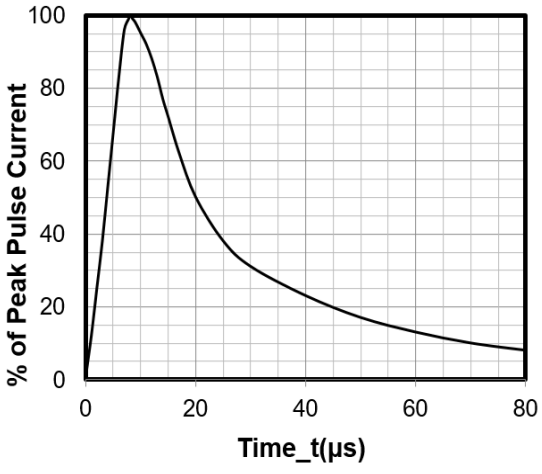
Peak Pulse Power vs. Pulse Time



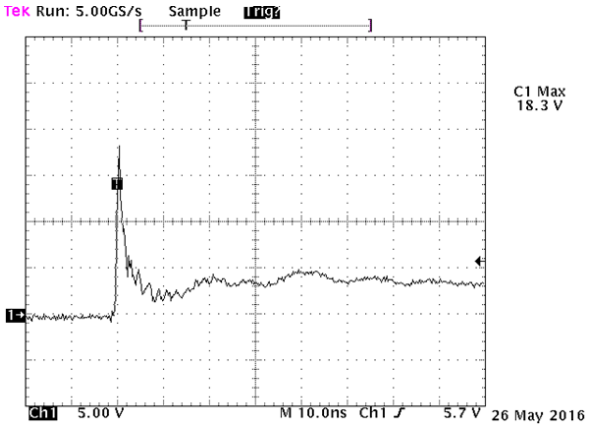
Clamping Voltage vs. Peak Pulse Current



Power Derating Curve



8 X 20μs Pulse Waveform

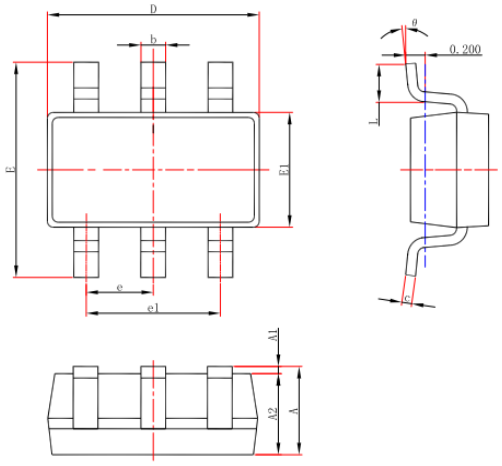


Note：Data is taken with a 10x attenuator

ESD Clamping Voltage

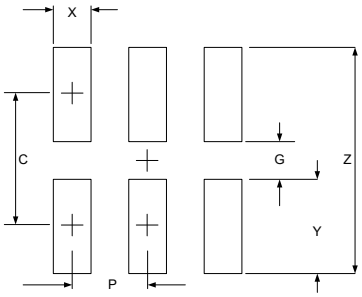
8 kV Contact per IEC61000−4−2

SOT23-6 Package Outline Drawing



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

Suggested Land Pattern



SYM	DIMENSIONS	
	MILLIMETERS	INCHES
C	2.50	0.098
G	1.40	0.055
P	0.95	0.037
X	0.60	0.024
Y	1.10	0.043
Z	3.60	0.141

Contact Information

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